N-Channel 60-V (D-S), 175°C MOSFET

PRODUCT SUMMARY		
$V_{(BR)DSS}$ (V)	$r_{DS(on)}$ (Ω)	I_D (A)
60	0.0093 @ V_{GS} = 10 V	90
	0.0135 @ V_{GS} = 4.5 V	62

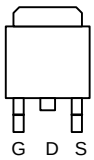
FEATURES

- TrenchFET® Power MOSFET
- 175°C Junction Temperature

APPLICATIONS

- 12-V Automotive Systems
  - Load Switch
  - Motor Drive
  - DC/DC

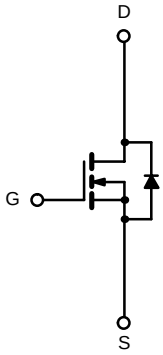
TO-263



Top View

DRAIN connected to TAB

SUM75N06-09L



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T_A = 25°C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current (T_J = 175°C)	T_C = 25°C	I_D	90	A
	T_C = 100°C		53	
Pulsed Drain Current		I_{DM}	160	
Avalanche Current		I_{AR}	50	
Repetitive Avalanche Energy[a]	L = 0.1 mH	E_{AR}	125	mJ
Power Dissipation	T_C = 25°C	P_D	125[b]	W
	T_A = 25°C[c]	P_D	3.75[c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 to 175	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Junction-to-Ambient (PCB Mount)[c]	R_{thJA}	40	°C/W
Junction-to-Case	R_{thJC}	1.2	

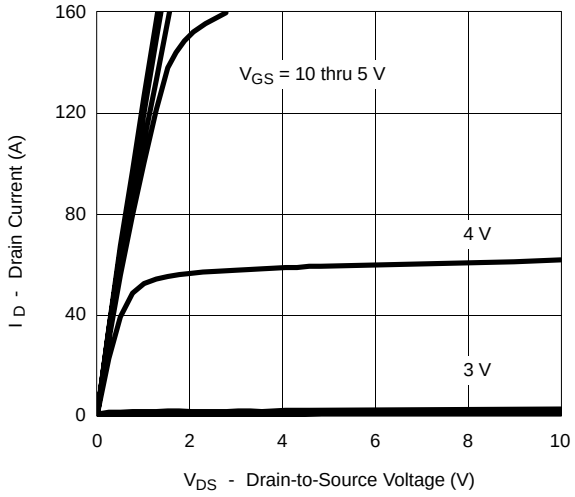
Notes:
a. Duty cycle ≤ 1%.
b. See SOA curve for voltage derating.
c. When mounted on 1" square PCB (FR-4 material).

MOSFET SPECIFICATIONS (T_J =25°C UNLESS OTHERWISE NOTED)						
Parameter	**Symbol**	**Test Condition**	**Min**	**Typ**	**Max**	**Unit**
Static						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA	60			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_{DS} = 250 μA	1	2	3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 60 V, V_{GS} = 0 V			1	μA
		V_{DS} = 60 V, V_{GS} = 0 V, T_J = 125°C			50	
		V_{DS} = 60 V, V_{GS} = 0 V, T_J = 175°C			150	
On-State Drain Current[a]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	75			A
Drain-Source On-State Resistance[a]	$r_{DS(on)}$	V_{GS} = 10 V, I_D = 30 A		0.0075	0.0093	Ω
		V_{GS} = 10 V, I_D = 30 A, T_J = 125°C			0.0163	
		V_{GS} = 10 V, I_D = 30 A, T_J = 175°C			0.024	
		V_{GS} = 4.5 V, I_D = 30 A		0.0105	0.0135	
		V_{GS} = 4.5 V, I_D = 30 A, T_J = 125°C			0.0224	
		V_{GS} = 4.5 V, I_D = 30 A, T_J = 175°C			0.030	
Forward Transconductance[a]	g_{fs}	V_{DS} = 15 V, I_D = 30 A	25	75		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz		2400		pF
Output Capacitance	C_{oss}			430		
Reversen Transfer Capacitance	C_{rss}			210		
Total Gate Charge[c]	Q_g	V_{DS} = 30 V, V_{GS} = 10 V, I_D = 90 A		47	75	nC
Gate-Source Charge[c]	Q_{gs}			12		
Gate-Drain Charge[c]	Q_{gd}			13		
Turn-On Delay Time[c]	$t_{d(on)}$	V_{DD} = 30 V, R_L = 0.4 Ω I_D ≃ 90 A, V_{GEN} = 10 V, R_G = 2.5 Ω		7	12	ns
Rise Time[c]	t_r			30	50	
Turn-Off Delay Time[c]	$t_{d(off)}$			25	40	
Fall Time[c]	t_f			12	20	
Source-Drain Diode Ratings and Characteristics (T_C = 25°C)[b]						
Continuous Current	I_s				90	A
Pulsed Current	I_{SM}			160	180	
Forward Voltage[a]	V_{SD}	I_F = 90 A, V_{GS} = 0 V			1.4	V
Reverse Recovery Time	t_{rr}	I_F = 50 A, di/dt = 100 A/μs		40	80	ns
Peak Reverse Recovery Current	$I_{RM(REC)}$			2	4	A
Reverse Recovery Charge	Q_{rr}			0.040	0.16	μC

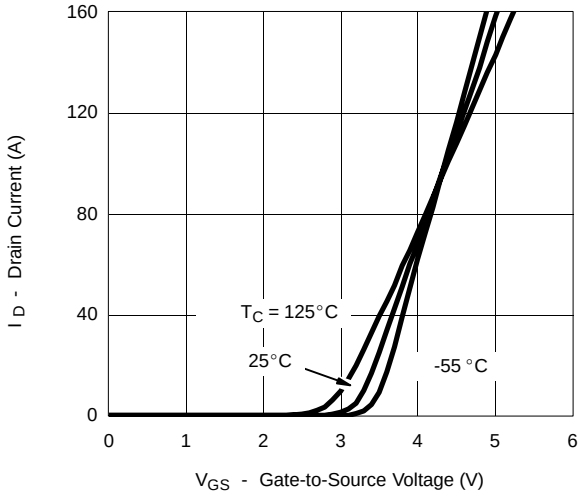
Notes:
a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
b. Guaranteed by design, not subject to production testing.
c. Independent of operating temperature.

TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

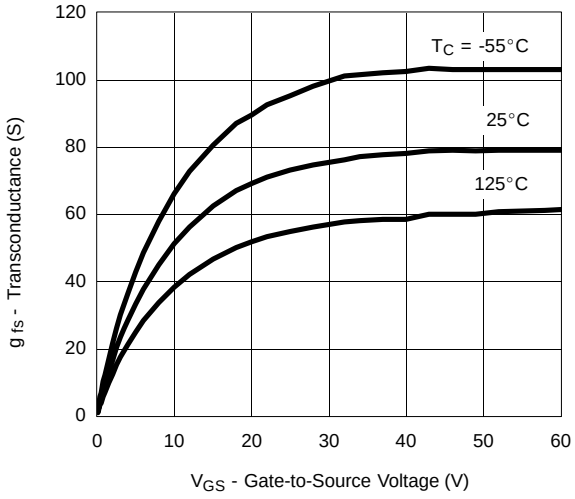
Output Characteristics



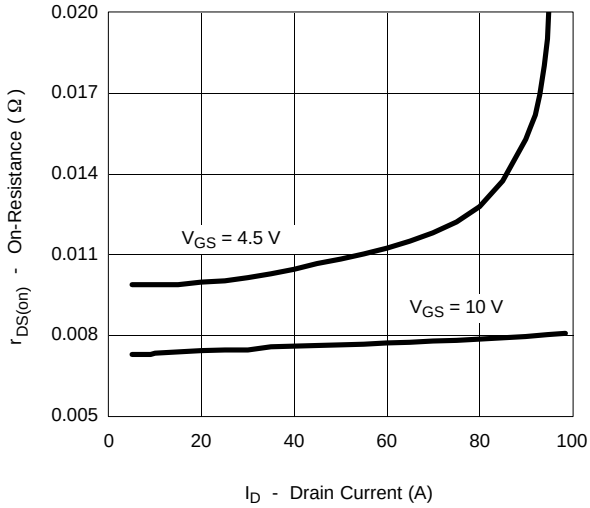
Transfer Characteristics



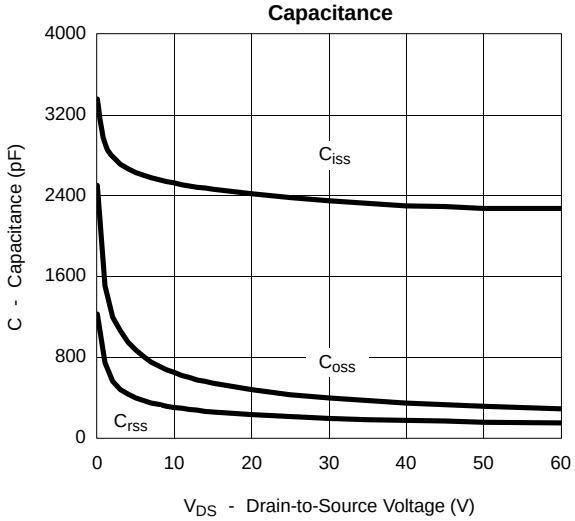
Transconductance



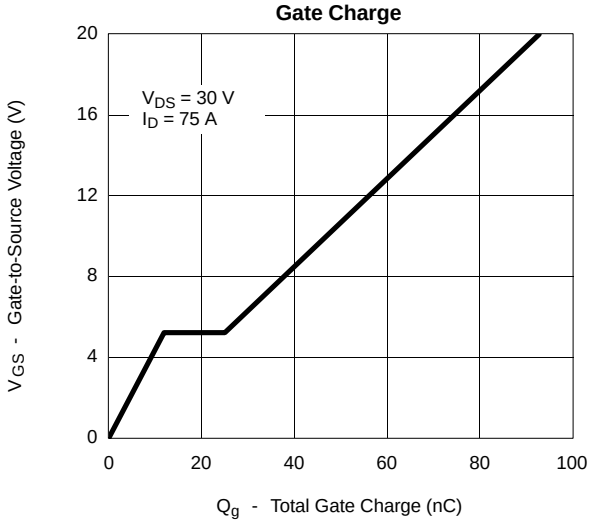
On-Resistance vs. Drain Current



Capacitance

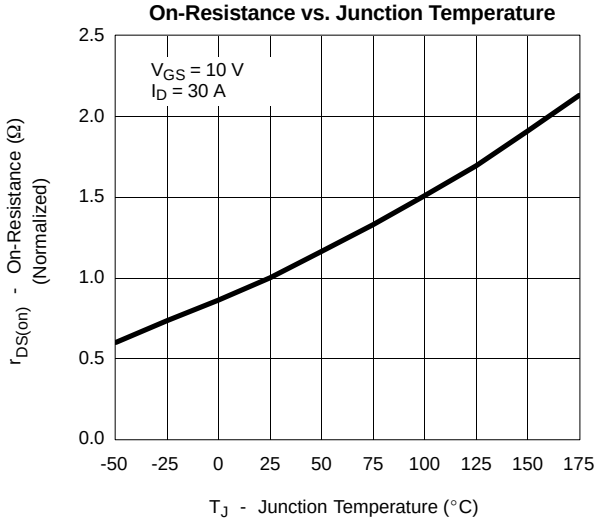


Gate Charge

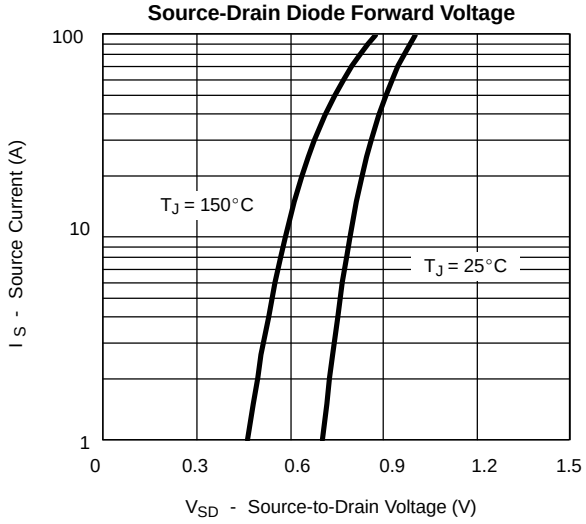


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

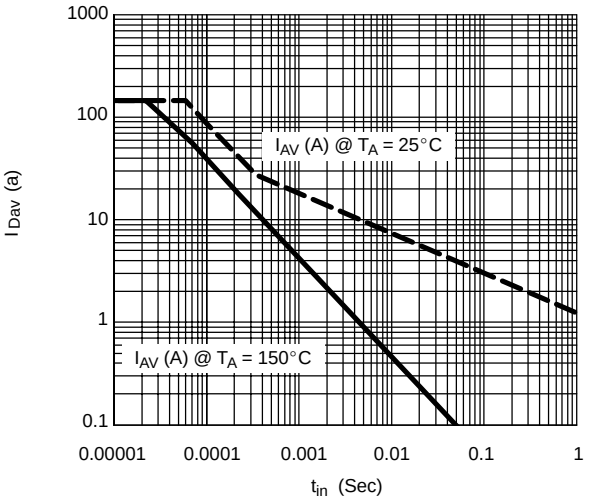
On-Resistance vs. Junction Temperature



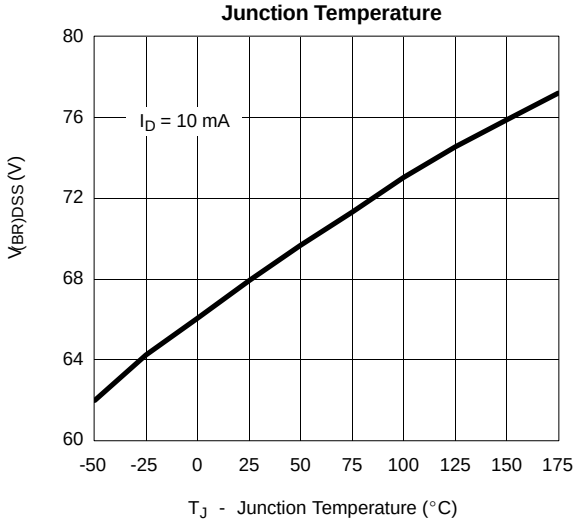
Source-Drain Diode Forward Voltage



Avalanche Current vs. Time

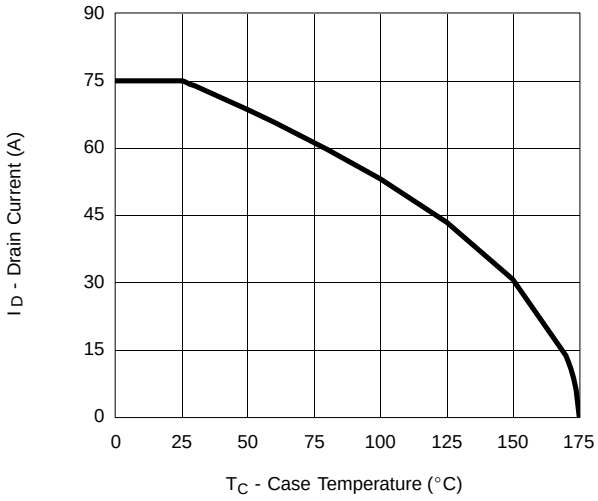


Drain Source Breakdown vs. Junction Temperature

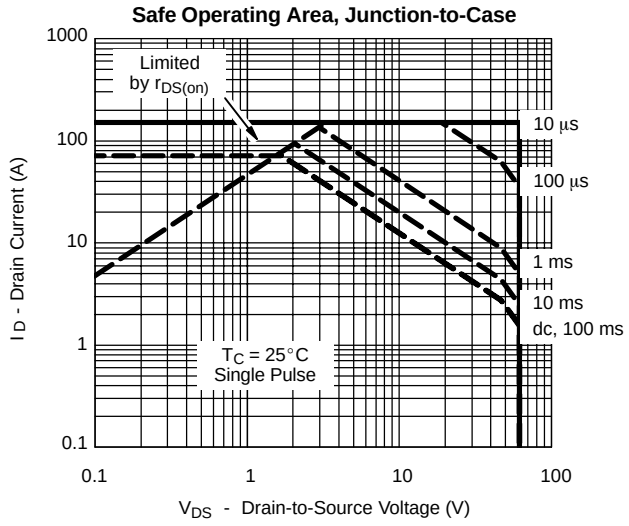


THERMAL RATINGS

Maximum Avalanche Drain Current vs. Case Temperature



Safe Operating Area, Junction-to-Case



Normalized Thermal Transient Impedance, Junction-to-Case